

Amendment to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

Claim 1 (Currently Amended): A method for fabricating a semiconductor device comprising the steps of:

forming a semiconductor film over a semiconductor substrate;

implanting a dopant into a ~~prescribed~~ first region of the semiconductor film where a resistance element is to be formed, a second region of the semiconductor film where a gate electrode is to be formed being not implanted with the dopant; and

patterning the semiconductor film to form ~~a resistance element~~ the resistance element of the semiconductor film with the dopant implanted, and ~~a gate electrode~~ the gate electrode of the semiconductor film with the dopant not implanted.

Claim 2 (Original): A method for fabricating a semiconductor device according to claim 1, further comprising, after the step of forming a gate electrode, the step of implanting a dopant into the gate electrode.

Claim 3 (Original): A method for fabricating a semiconductor device according to claim 2, wherein

in the step of implanting the dopant into the gate electrode, the dopant is implanted into the semiconductor substrate on both sides of the gate electrode to form a dopant diffused region.

Claim 4 (Original): A method for fabricating a semiconductor device according to claim 2, wherein

in the step of forming the gate electrode, a first gate electrode and a second gate electrode are formed, and

in the step of implanting the dopant into the gate electrode, a first conduction type dopant is implanted into the first gate electrode, and a second conduction type dopant is implanted into the second gate electrode.

Claim 5 (Original): A method for fabricating a semiconductor device according to claim 3, wherein

in the step of forming the gate electrode, a first gate electrode and a second gate electrode are formed, and

in the step of implanting the dopant into the gate electrode, a first conduction type dopant is implanted into the first gate electrode, and a second conduction type dopant is implanted into the second gate electrode.

Claim 6 (Original): A method for fabricating a semiconductor device according to claim 1, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is implanted into a plurality of regions of the prescribed region in concentrations different from each other to form a plurality of the resistance elements of resistance values different from each other.

Claim 7 (Original): A method for fabricating a semiconductor device according to claim 2, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is implanted into a plurality of regions of the prescribed region in concentrations different from each other to form a plurality of the resistance elements of resistance values different from each other.

Claim 8 (Original): A method for fabricating a semiconductor device according to claim 3, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is implanted into a plurality of regions of the prescribed region in concentrations different from each other to form a plurality of the resistance elements of resistance values different from each other.

Claim 9 (Original): A method for fabricating a semiconductor device according to claim 1, further comprising, after the step of forming the gate electrode, the steps of:

forming an insulation film for covering the gate electrode and the resistance element; and
etching the insulation film to leave the insulation film on the resistance element and form a sidewall insulation film on the side wall of the gate electrode.

Claim 10 (Original): A method for fabricating a semiconductor device according to claim 2, further comprising, after the step of forming the gate electrode, the steps of:

forming an insulation film for covering the gate electrode and the resistance element; and
etching the insulation film to leave the insulation film on the resistance element and form a sidewall insulation film on the side wall of the gate electrode.

Claim 11 (Original): A method for fabricating a semiconductor device according to claim 3, further comprising, after the step of forming the gate electrode, the steps of:

forming an insulation film for covering the gate electrode and the resistance element; and
etching the insulation film to leave the insulation film on the resistance element and form a sidewall insulation film on the side wall of the gate electrode.

Claim 12 (Original): A method for fabricating a semiconductor device according to claim 9, further comprising, after the step of forming the sidewall insulation film, the step of

forming a metal film on the semiconductor substrate with the gate electrode formed on, performing thermal processing to silicide the metal film to thereby form a silicide film on the gate electrode and the semiconductor substrate on both sides of the gate electrode.

Claim 13 (Original): A method for fabricating a semiconductor device according to claim 10, further comprising, after the step of forming the sidewall insulation film, the step of forming a metal film on the semiconductor substrate with the gate electrode formed on, performing thermal processing to silicide the metal film to thereby form a silicide film on the gate electrode and the semiconductor substrate on both sides of the gate electrode.

Claim 14 (Original): A method for fabricating a semiconductor device according to claim 1, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is ion implanted at a $1 \times 10^{15} \text{ cm}^{-2}$ dose or above.

Claim 15 (Original): A method for fabricating a semiconductor device according to claim 2, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is ion implanted at a $1 \times 10^{15} \text{ cm}^{-2}$ dose or above.

Claim 16 (Original): A method for fabricating a semiconductor device according to claim 3, wherein

in the step of implanting the dopant into the semiconductor film, the dopant is ion implanted at a $1 \times 10^{15} \text{ cm}^{-2}$ dose or above.

Claim 17 (Original): A method for fabricating a semiconductor device according to

claim 1, wherein

in the step of forming the semiconductor film, the semiconductor film is formed of polysilicon or amorphous silicon.

Claim 18 (Original): A method for fabricating a semiconductor device according to claim 2, wherein

in the step of forming the semiconductor film, the semiconductor film is formed of polysilicon or amorphous silicon.

Claim 19 (Original): A method for fabricating a semiconductor device according to claim 3, wherein

in the step of forming the semiconductor film, the semiconductor film is formed of polysilicon or amorphous silicon.